

## Transistors

## 2.5V Drive Nch+SBD MOS FET

## US5U1

## ●Structure

Silicon N-channel MOS FET /  
Schottky barrier diode

## ●Features

- 1) Nch MOS FET and schottky barrier diode are put in TUMT5 package.
- 2) High-speed switching, Low On-resistance.
- 3) Low voltage drive (2.5V drive).
- 4) Built-in Low  $V_F$  schottky barrier diode.

## ●Applications

Switching

## ●Package specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
US5U1		○

●Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

<MOS FET>

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DS}$	30	V	
Gate-source voltage	$V_{GS}$	12	V	
Drain current	Continuous	$I_D$	$\pm 1.5$	A
	Pulsed	$I_{DP}$ *1	$\pm 6.0$	A
Source current (Body diode)	Continuous	$I_S$	0.75	A
	Pulsed	$I_{SP}$ *1	6.0	A
Power dissipation	$P_D$ *2	0.7	W / ELEMENT	
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$	

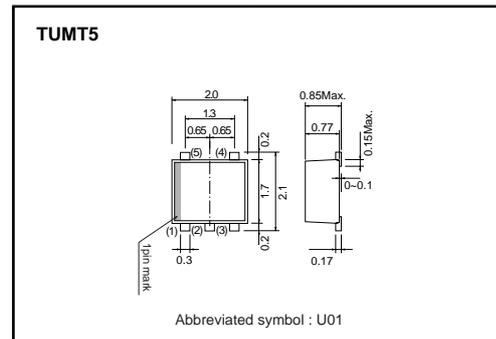
\*1  $P_{ws} \leq 10\mu\text{s}$ , Duty cycles  $\leq 1\%$   
\*2 Mounted on a ceramic board

<Di>

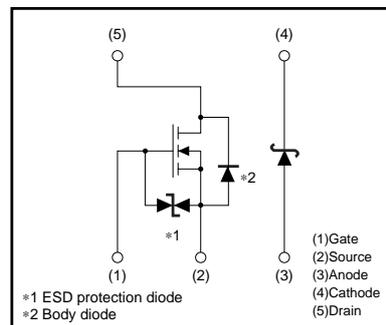
Parameter	Symbol	Limits	Unit
Repetitive peak reverse voltage	$V_{RM}$	30	V
Reverse voltage	$V_R$	20	V
Forward current	$I_F$	0.5	A
Forward current surge peak	$I_{FSM}$ *1	2.0	A
Power dissipation	$P_D$ *2	0.5	W / ELEMENT
Junction temperature	$T_j$	150	$^\circ\text{C}$

\*1 60Hz  $\cdot$  1cycle  
\*2 Mounted on ceramic board

## ●External dimensions (Unit : mm)



## ●Inner circuit



## Transistors

&lt;MOS FET and Di&gt;

Parameter	Symbol	Limits	Unit
Total power dissipation	$P_D$ *1	1.0	W / TOTAL
Range of storage temperature	$T_{stg}$	-55 to +150	°C

\*1 Mounted on a ceramic board

## ●Electrical characteristics (Ta=25°C)

&lt;MOS FET&gt;

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	10	$\mu A$	$V_{GS}=12V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu A$	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.5	-	1.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	-	170	240	$m\Omega$	$I_D=1.5A, V_{GS}=4.5V$
		-	180	250	$m\Omega$	$I_D=1.5A, V_{GS}=4V$
		-	240	340	$m\Omega$	$I_D=1.5A, V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $ *	1.5	-	-	S	$V_{DS}=10V, I_D=1.5A$
Input capacitance	$C_{iss}$	-	80	-	pF	$V_{DS}=10V$
Output capacitance	$C_{oss}$	-	14	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	-	12	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	-	7	-	ns	$V_{DD}=15V$
Rise time	$t_r$ *	-	9	-	ns	$I_D=0.75A$
Turn-off delay time	$t_{d(off)}$ *	-	15	-	ns	$V_{GS}=4.5V$
Fall time	$t_f$ *	-	6	-	ns	$R_L=20\Omega$
Total gate charge	$Q_g$ *	-	1.6	2.2	nC	$V_{DD}=15V, V_{GS}=4.5V$
Gate-source charge	$Q_{gs}$ *	-	0.5	-	nC	$I_D=1.5A$
Gate-drain charge	$Q_{gd}$ *	-	0.3	-	nC	$R_L=10\Omega, R_G=10\Omega$

\*Pulsed

&lt;Body diode characteristics (Source-drain)&gt;

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}$	-	-	1.2	V	$I_S=0.75A, V_{GS}=0V$

&lt;Di&gt;

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.36	V	$I_S=0.1A$
		-	-	0.47	V	$I_S=0.5A$
Reverse current	$I_R$	-	-	100	$\mu A$	$I_S=20V$

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